

P-Channel Enhancement Mode Power MOSFET

Description

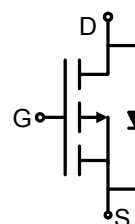
The PT6C03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

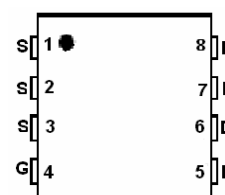
- $V_{DS} = -20V, I_D = -20A$
- $R_{DS(ON)} < 28m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} < 40m\Omega @ V_{GS} = -2.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- Motor drive
- Load switch
- Power management



Schematic diagram



Marking and pin assignment

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
PT GEÜGÖ	PT GEÜGÖ	ÖpíYîĚŠ	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-20	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-60	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	42	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250\mu A$	-20	-	-	V

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.7	-1.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-6A$	-	22	28	m Ω
		$V_{GS}=-2.5V, I_D=-5A$		32	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-6A$	-	17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	2100	-	PF
Output Capacitance	C_{OSS}		-	498	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega,$ $V_{GS}=-4.5V, R_{GEN}=6\Omega$	-	25	-	nS
Turn-on Rise Time	t_r		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	70	-	nS
Turn-Off Fall Time	t_f		-	50	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-6A, V_{GS}=-4.5V$	-	17	-	nC
Gate-Source Charge	Q_{gs}		-	4.1	-	nC
Gate-Drain Charge	Q_{gd}		-	4.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-20A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

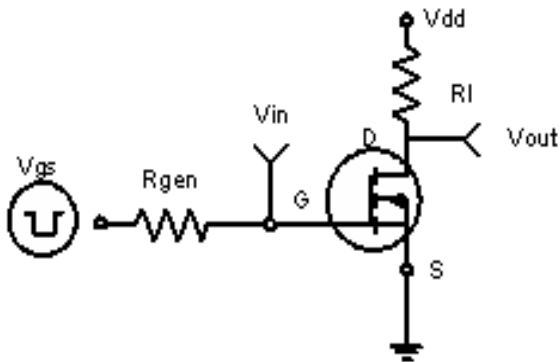


Figure 1 Switching Test Circuit

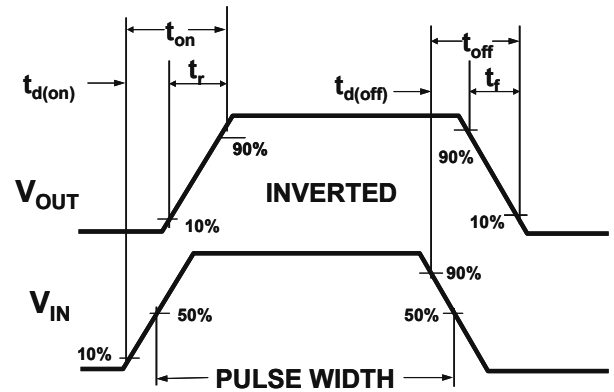


Figure 2 Switching Waveforms

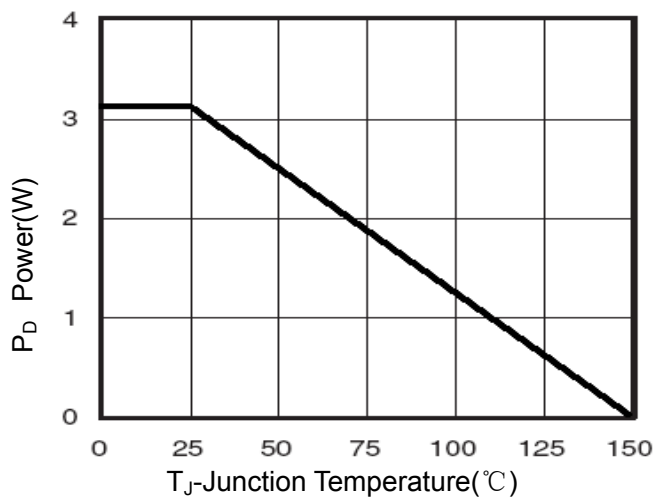


Figure 3 Power Dissipation

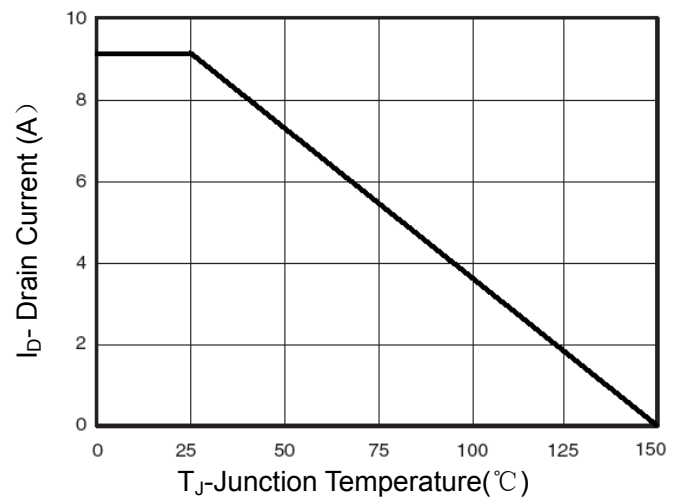


Figure 4 Drain Current

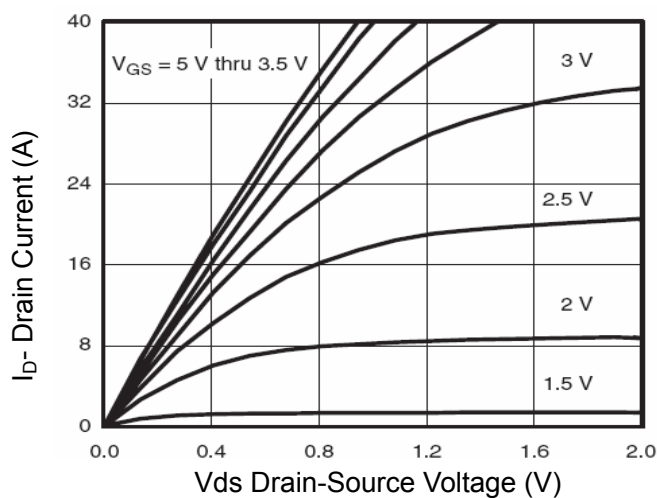


Figure 5 Output Characteristics

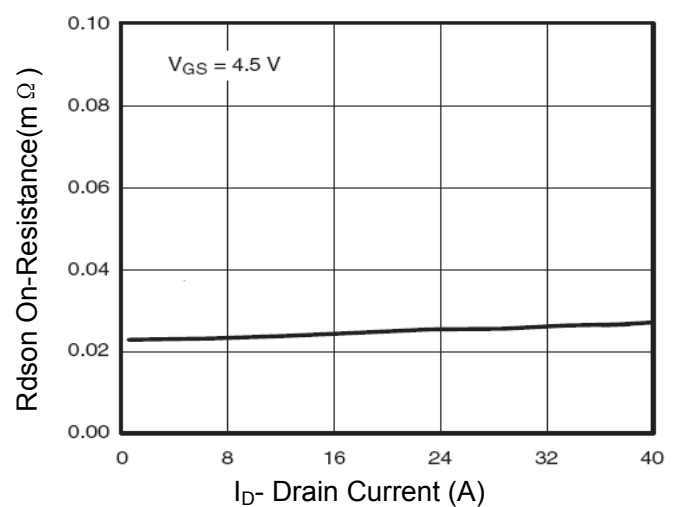


Figure 6 Drain-Source On-Resistance

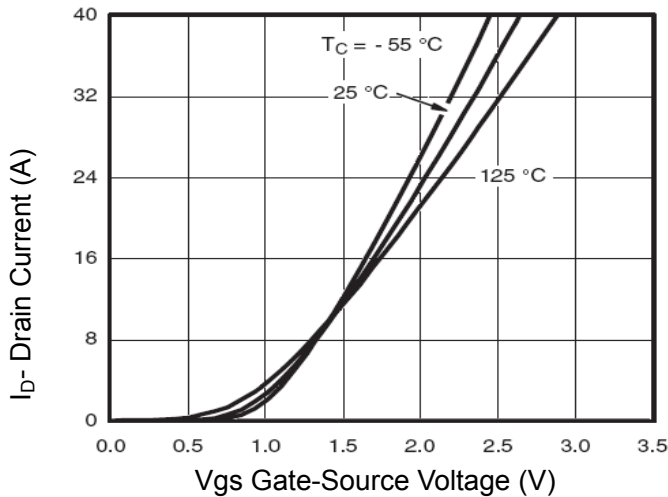


Figure 7 Transfer Characteristics

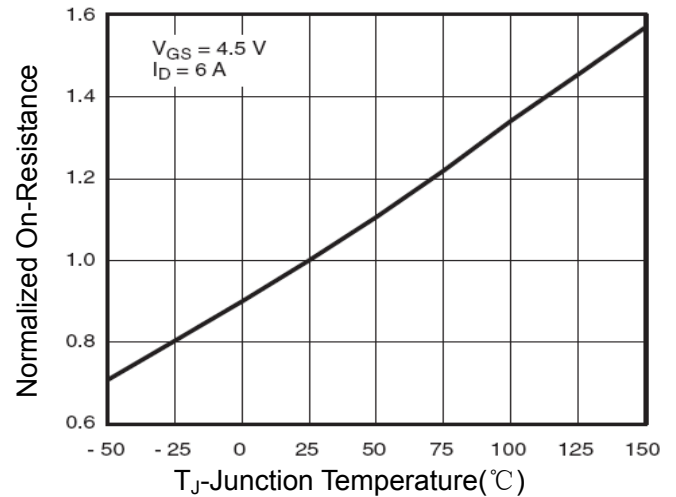


Figure 8 Drain-Source On-Resistance

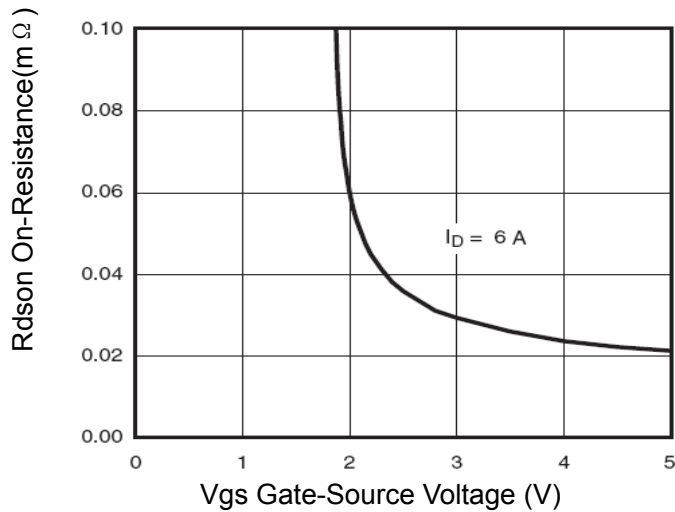


Figure 9 Rdson vs Vgs

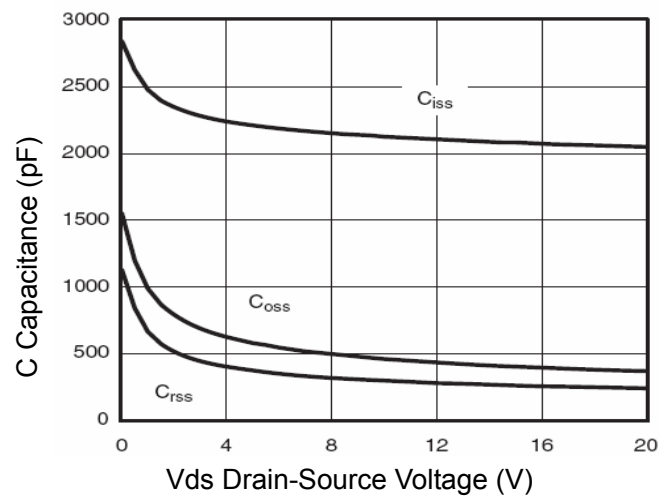


Figure 10 Capacitance vs Vds

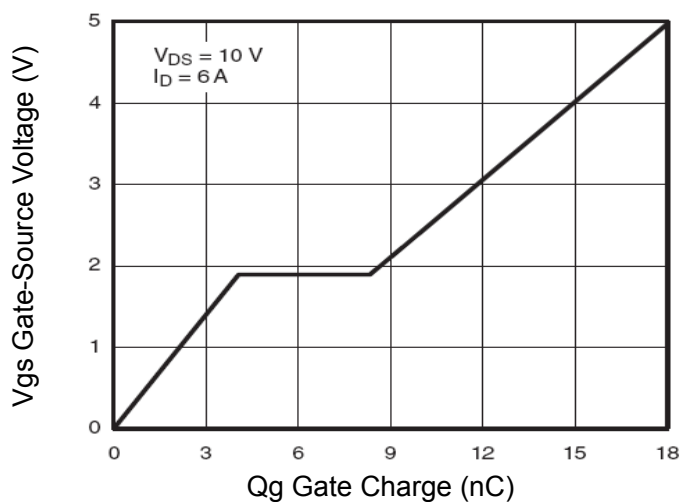


Figure 11 Gate Charge

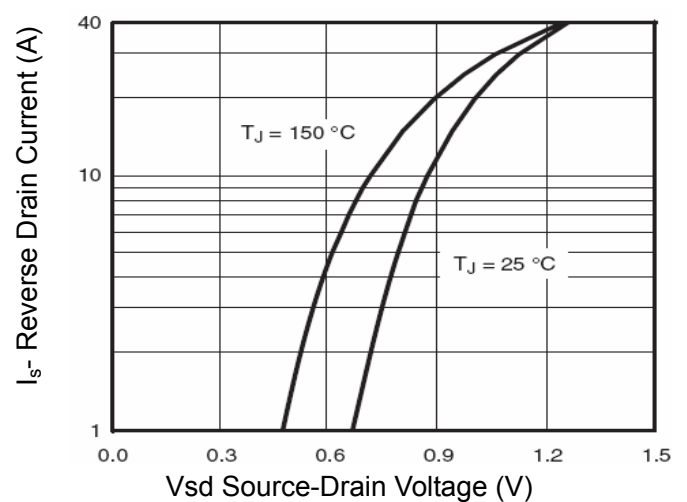
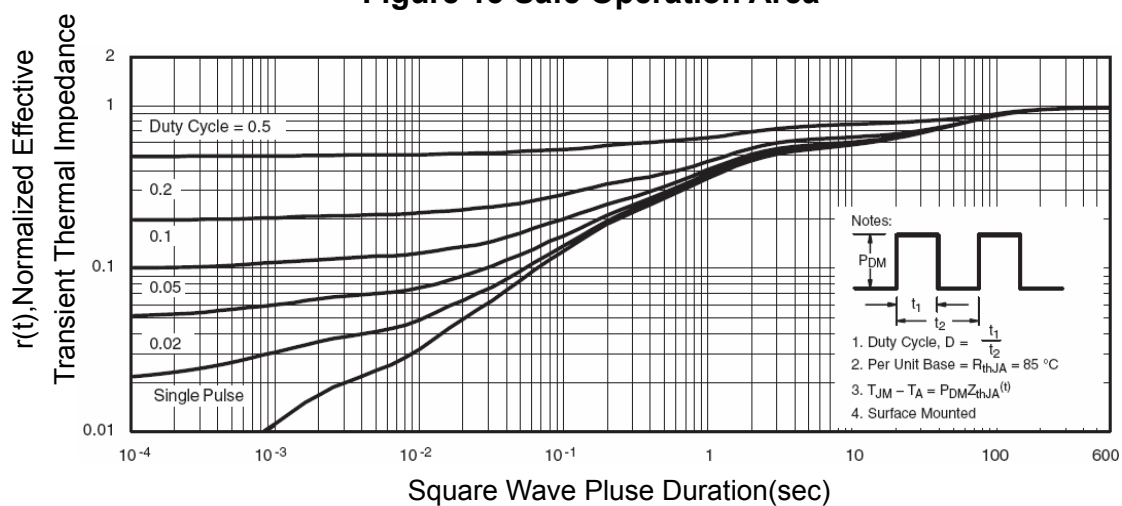
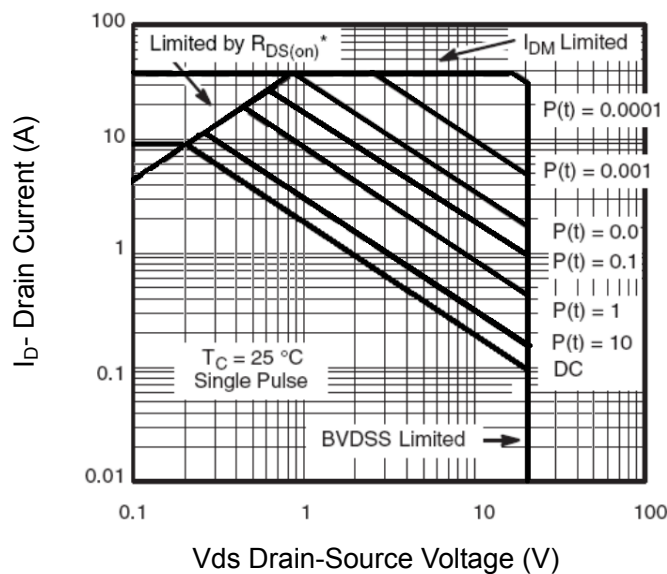


Figure 12 Source- Drain Diode Forward



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